

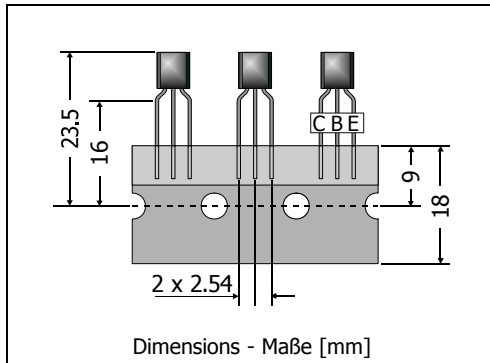
2N3906

PNP

Si-Epitaxial-Planar Switching Transistors
Si-Epitaxial-Planar Schalttransistoren

PNP

Version 2006-09-12


 Power dissipation
 Verlustleistung

625 mW

 Plastic case
 Kunststoffgehäuse

 TO-92
 (10D3)

Weight approx. – Gewicht ca.

0.18 g

 Plastic material has UL classification 94V-0
 Gehäusematerial UL94V-0 klassifiziert

 Standard packaging taped in ammo pack
 Standard Lieferform getupet in Ammo-Pack
Maximum ratings ($T_A = 25^\circ\text{C}$)Grenzwerte ($T_A = 25^\circ\text{C}$)

			2N3906
Collector-Emitter-volt. – Kollektor-Emitter-Spannung	B open	- V_{CEO}	40 V
Collector-Base-voltage – Kollektor-Basis-Spannung	E open	- V_{CBO}	40 V
Emitter-Base-voltage – Emitter-Basis-Spannung	C open	- V_{EBO}	5 V
Power dissipation – Verlustleistung		P_{tot}	625 mW ¹⁾
Collector current – Kollektorstrom (dc)		- I_C	200 mA
Junction temperature – Sperrschichttemperatur		T_j	-55...+150°C
Storage temperature – Lagerungstemperatur		T_s	-55...+150°C

Characteristics ($T_j = 25^\circ\text{C}$)Kennwerte ($T_j = 25^\circ\text{C}$)

		Min.	Typ.	Max.
DC current gain – Kollektor-Basis-Stromverhältnis ²⁾				
- $I_C = 0.1\text{ mA}$, - $V_{CE} = 1\text{ V}$	h_{FE}	60	–	–
- $I_C = 1\text{ mA}$, - $V_{CE} = 1\text{ V}$	h_{FE}	80	–	–
- $I_C = 10\text{ mA}$, - $V_{CE} = 1\text{ V}$	h_{FE}	100	–	300
- $I_C = 50\text{ mA}$, - $V_{CE} = 1\text{ V}$	h_{FE}	60	–	–
- $I_C = 100\text{ mA}$, - $V_{CE} = 1\text{ V}$	h_{FE}	30	–	–
Collector-Emitter saturation voltage – Kollektor-Emitter-Sättigungsspg. ²⁾				
- $I_C = 10\text{ mA}$, - $I_B = 1\text{ mA}$	- V_{CEsat}	–	–	0.25 V
- $I_C = 50\text{ mA}$, - $I_B = 5\text{ mA}$	- V_{CEsat}	–	–	0.40 V
Base-Emitter saturation voltage – Basis-Emitter-Sättigungsspannung ²⁾				
- $I_C = 10\text{ mA}$, - $I_B = 1\text{ mA}$	- V_{BEsat}	0.65 V	–	0.85 V
- $I_C = 50\text{ mA}$, - $I_B = 5\text{ mA}$	- V_{BEsat}	–	–	0.95 V

1 Mounted on P.C. board with 3 mm² copper pad at each terminal
 Montage auf Leiterplatte mit 3 mm² Kupferbelag (Lötpad) an jedem Anschluss

2 Tested with pulses $t_p = 300\ \mu\text{s}$, duty cycle $\leq 2\%$ – Gemessen mit Impulsen $t_p = 300\ \mu\text{s}$, Schaltverhältnis $\leq 2\%$

Characteristics (T_j = 25°C)
Kennwerte (T_j = 25°C)

		Min.	Typ.	Max.
Collector-Emitter cutoff current – Kollektor-Emitter-Reststrom - V _{CE} = 30 V, - V _{EB} = 3 V	- I _{CBX}	–	–	50 nA
Emitter-Base cutoff current – Emitter-Basis-Reststrom - V _{CE} = 30 V, - V _{EB} = 3 V	- I _{EBV}	–	–	50 nA
Gain-Bandwidth Product – Transitfrequenz - I _C = 10 mA, - V _{CE} = 20 V, f = 100 MHz	f _T	250 MHz	–	–
Collector-Base Capacitance – Kollektor-Basis-Kapazität - V _{CB} = 5 V, I _E = i _e = 0, f = 1 MHz	C _{CB0}	–	–	4.5 pF
Emitter-Base Capacitance – Emitter-Basis-Kapazität - V _{EB} = 0.5 V, I _C = i _c = 0, f = 1 MHz	C _{EBO}	–	–	10 pF
Noise figure – Rauschzahl - V _{CE} = 5 V, - I _C = 100 μA, R _G = 1 kΩ, f = 1 kHz	F	–	–	4 dB
Switching times – Schaltzeiten (between 10% and 90% levels)				
delay time - V _{CC} = 3 V, - V _{BE} = 0.5 V	t _d	–	–	35 ns
rise time - I _C = 10 mA, - I _{B1} = 1mA	t _r	–	–	35 ns
storage time - V _{CC} = 3 V, - I _C = 10 mA,	t _s	–	–	225 ns
fall time - I _{B1} = - I _{B2} = 1 mA	t _f	–	–	75 ns
Thermal resistance junction to ambient air Wärmewiderstand Sperrschicht – umgebende Luft	R _{thA}	< 200 K/W ¹⁾		
Recommended complementary NPN transistors Empfohlene komplementäre NPN-Transistoren		2N3904		

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Montage auf Leiterplatte mit 3 mm² Kupferbelag (Löt-pad) an jedem Anschluss